DATA SHEET

74LVT573

3.3V Octal D-type transparent latch (3-State)

Product specification
Supersedes data of 1995 Nov 14
IC23 Data Handbook

1998 Feb 19

Philips
Semiconductors

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3.3V Octal D-type transparent latch (3-State)

74LVT573

FEATURES

- Inputs and outputs on opposite side of package allow easy interface to microprocessors
- 3-State output buffers
- Common output enable
- TTL input and output switching levels
- Input and output interface capability to systems at 5V supply
- Bus-hold data inputs eliminate the need for external pull-up resistors to hold unused inputs
- Live insertion/extraction permitted
- No bus current loading when output is tied to 5V bus
- Latch-up protection exceeds 500mA per JEDEC Std 17
- Power-up 3-State
- Power-up reset
- ESD protection exceeds 2000V per MIL STD 883 Method 3015 and 200V per Machine Model

DESCRIPTION

The LVT573 is a high-performance BiCMOS product designed for VCC operation at 3.3V. This device is an octal transparent latch coupled to eight 3-State output buffers. The two sections of the device are controlled independently by Enable (E) and Output Enable ($\overline{OE}$) control gates. The 74LVT573 has a broadside pinout configuration to facilitate PC board layout and allow easy interface with microprocessors.

The data on the D inputs are transferred to the latch outputs when the Latch Enable (E) input is High. The latch remains transparent to the data inputs while E is High, and stores the data that is present one setup time before the High-to-Low enable transition.

The 3-State output buffers are designed to drive heavily loaded 3-State buses, MOS memories, or MOS microprocessors. The active-Low Output Enable ($\overline{OE}$) controls all eight 3-State buffers independent of the latch operation.

When $\overline{OE}$ is Low, the latched or transparent data appears at the outputs. When $\overline{OE}$ is High, the outputs are in the High-impedance "OFF" state, which means they will neither drive nor load the bus.

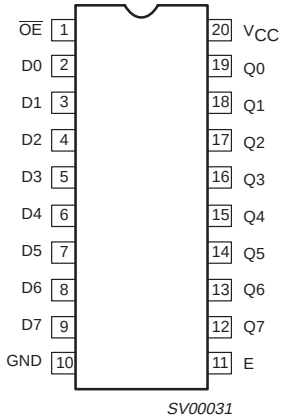
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS T_{amb} = 25°C; GND = 0V	TYPICAL	UNIT
t_{PLH} t_{PHL}	Propagation delay Dn to Qn	C_L = 50pF; V_{CC} = 3.3V	2.5 2.7	ns
C_{IN}	Input capacitance	V_I = 0V or 3.0V	4	pF
C_{OUT}	Output capacitance	Outputs disabled; V_O = 0V or 3.0V	8	pF
I_{CCZ}	Total supply current	Outputs disabled; V_{CC} = 3.6V	.13	mA

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
20-Pin Plastic SOL	–40°C to +85°C	74LVT573 D	74LVT573 D	SOT163-1
20-Pin Plastic SSOP Type II	–40°C to +85°C	74LVT573 DB	74LVT573 DB	SOT339-1
20-Pin Plastic TSSOP Type I	–40°C to +85°C	74LVT573 PW	74LVT573PW DH	SOT360-1

PIN CONFIGURATION

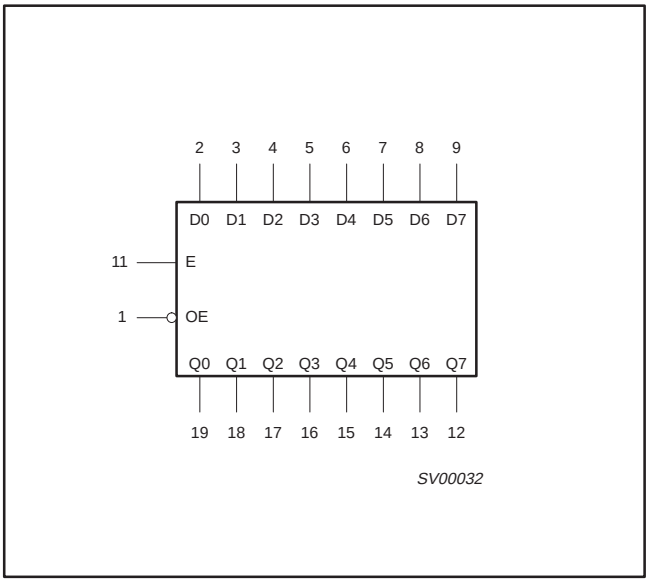


SV00031

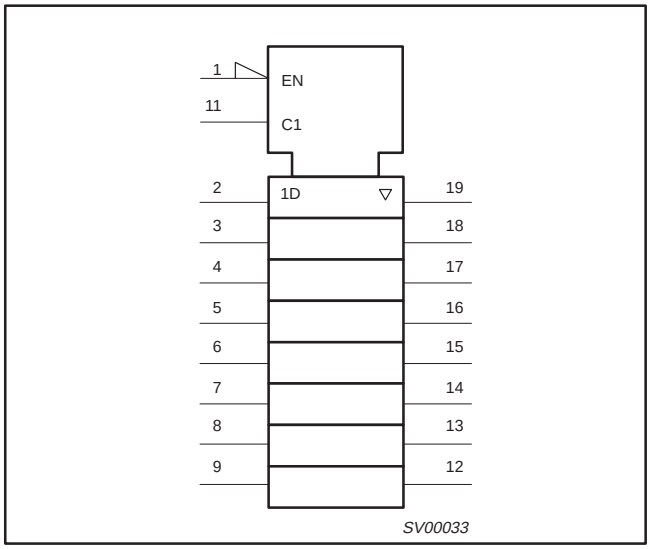
PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
1	$\overline{OE}$	Output enable input (active-Low)
2, 3, 4, 5, 6, 7, 8, 9	D0-D7	Data inputs
19, 18, 17, 16, 15, 14, 13, 12	Q0-Q7	Data outputs
11	E	Enable input (active-High)
10	GND	Ground (0V)
20	V_{CC}	Positive supply voltage

LOGIC SYMBOL



LOGIC SYMBOL (IEEE/IEC)

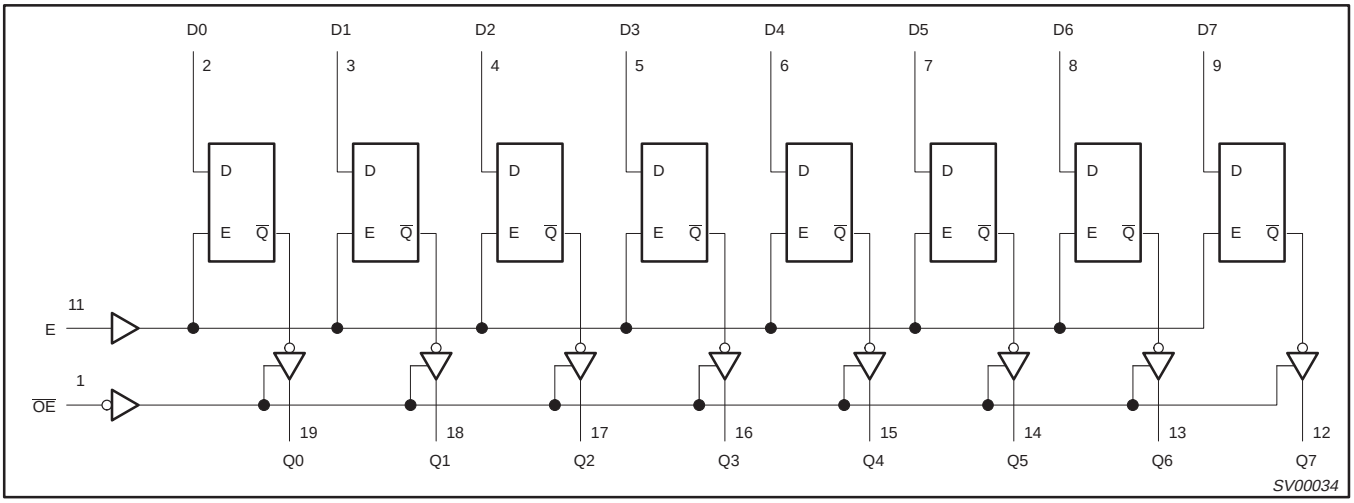


FUNCTION TABLE

INPUTS			INTERNAL REGISTER	OUTPUTS	OPERATING MODE
$\overline{OE}$	E	Dn		Q0 – Q7	
L L	H H	L H	L H	L H	Enable and read register
L L	↓ ↓	l h	L H	L H	Latch and read register
L	L	X	NC	NC	Hold
H	X	X	NC	Z	Disable outputs

H = High voltage level
h = High voltage level one set-up time prior to the High-to-Low E transition
L = Low voltage level
l = Low voltage level one set-up time prior to the High-to-Low E transition
NC = No change
X = Don't care
Z = High impedance "off" state
↓ = High-to-Low E transition

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS[1, 2]

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V_{CC}	DC supply voltage		–0.5 to +4.6	V
I_{IK}	DC input diode current	$V_I < 0$	–50	mA
V_I	DC input voltage[3]		–0.5 to +7.0	V
I_{OK}	DC output diode current	$V_O < 0$	–50	mA
V_{OUT}	DC output voltage[3]	Output in Off or High state	–0.5 to +7.0	V
I_{OUT}	DC output current	Output in Low state	128	mA
		Output in High state	–64	
T_{stg}	Storage temperature range		–65 to 150	°C

NOTES:
1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
3. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS		UNIT
		MIN	MAX	
V_{CC}	DC supply voltage	2.7	3.6	V
V_I	Input voltage	0	5.5	V
V_{IH}	High-level input voltage	2.0		V
V_{IL}	Input voltage		0.8	V
I_{OH}	High-level output current		–32	mA
I_{OL}	Low-level output current		32	mA
	Low-level output current; current duty cycle ≤ 50%, f ≥ 1kHz		64	
$\Delta t/\Delta v$	Input transition rise or fall rate; outputs enabled		10	ns/V
T_{amb}	Operating free-air temperature range	–40	+85	°C

DC ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	TEST CONDITIONS		LIMITS			UNIT
				Temp = -40°C to +85°C			
				MIN	TYP[1]	MAX	
V_{IK}	Input clamp voltage	V_{CC} = 2.7V; I_{IK} = –18mA			–0.9	–1.2	V
V_{OH}	High-level output voltage	V_{CC} = 2.7 to 3.6V; I_{OH} = –100µA		V_{CC}-0.2	V_{CC}-0.1		V
		V_{CC} = 2.7V; I_{OH} = –8mA		2.4	2.5		
		V_{CC} = 3.0V; I_{OH} = –32mA		2.0	2.2		
V_{OL}	Low-level output voltage	V_{CC} = 2.7V; I_{OL} = 100µA			0.1	0.2	V
		V_{CC} = 2.7V; I_{OL} = 24mA			0.3	0.5	
		V_{CC} = 3.0V; I_{OL} = 16mA			0.25	0.4	
		V_{CC} = 3.0V; I_{OL} = 32mA			0.3	0.5	
		V_{CC} = 3.0V; I_{OL} = 64mA			0.4	0.55	
V_{RST}	Power-up output low voltage[5]	V_{CC} = 3.6V; I_O = 1mA; V_I = GND or V_{CC}			0.13	0.55	V
I_I	Input leakage current	V_{CC} = 0 or 3.6V; V_I = 5.5V			1	10	µA
		V_{CC} = 3.6V; V_I = V_{CC} or GND	Control pins		±0.1	±1	
		V_{CC} = 3.6V; V_I = V_{CC}	Data pins[4]		0.1	1	
		V_{CC} = 3.6V; V_I = 0			–1	-5	
I_{OFF}	Output off current	V_{CC} = 0V; V_I or V_O = 0 to 4.5V			1	±100	µA
I_{HOLD}	Bus Hold current A inputs[7]	V_{CC} = 3V; V_I = 0.8V		75	150		µA
		V_{CC} = 3V; V_I = 2.0V		–75	–150		
		V_{CC} = 0V to 3.6V; V_{CC} = 3.6V		±500			
I_{EX}	Current into an output in the High state when $V_O > V_{CC}$	V_O = 5.5V; V_{CC} = 3.0V			60	125	µA
$I_{PU/PD}$	Power up/down 3-State output current[3]	$V_{CC} \leq$ 1.2V; V_O = 0.5V to V_{CC}; V_I = GND or V_{CC}; $\overline{OE}$/OE = Don't care			1	±100	µA
I_{OZH}	3-State output High current	V_{CC}= 3.6V; V_O = 3V; V_I = V_{IL} or V_{IH}			1	5	µA
I_{OZL}	3-State output Low current	V_{CC}= 3.6V; V_O = 0.5V; V_I = V_{IL} or V_{IH}			–1	–5	
I_{CCH}	Quiescent supply current	V_{CC} = 3.6V; Outputs High, V_I = GND or V_{CC}, I_O = 0			0.13	0.19	mA
I_{CCL}		V_{CC} = 3.6V; Outputs Low, V_I = GND or V_{CC}, I_O = 0			3	12	
I_{CCZ}		V_{CC} = 3.6V; Outputs Disabled; V_I = GND or V_{CC}, I_O = 0[5]			0.13	0.19	
ΔI_{CC}	Additional supply current per input pin[2]	V_{CC} = 3V to 3.6V; One input at V_{CC}-0.6V, Other inputs at V_{CC} or GND			0.1	0.2	mA

NOTES:
1. All typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.
2. This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND
3. This parameter is valid for any V_{CC} between 0V and 1.2V with a transition time of up to 10msec. From V_{CC} = 1.2V to V_{CC} = 3.3V ± 0.3V a transition time of 100µsec is permitted. This parameter is valid for T_{amb} = 25°C only
4. Unused pins at V_{CC} or GND.
5. For valid test results, data must not be loaded into the flip-flops (or latches) after applying the power.
6. I_{CCZ} is measured with outputs pulled to V_{CC} or GND.
7. This is the bus hold overdrive current required to force the input to the opposite logic state.

AC CHARACTERISTICS

GND = 0V, $t_R = t_F$ = 2.5ns, C_L = 50pF, R_L = 500Ω; T_{amb} = –40°C to +85°C.

SYMBOL	PARAMETER	WAVEFORM	LIMITS				UNIT
			V_{CC} = 3.3V ± 0.3V			V_{CC} = 2.7V	
			MIN	TYP[1]	MAX	MAX	
t_{PLH} t_{PHL}	Propagation delay Dn to Qn	2	1.0 1.0	2.5 2.7	4.2 4.3	4.7 5.2	ns
t_{PLH} t_{PHL}	Propagation delay E to Qn	1	1.6 2.5	3.5 4.3	5.6 6.5	6.3 7.2	ns
t_{PZH} t_{PZL}	Output enable time to High and Low level	4 5	1.0 1.3	2.8 3.3	5.1 5.5	6.2 6.6	ns
t_{PHZ} t_{PLZ}	Output disable time from High and Low level	4 5	2.0 1.5	3.7 3.0	5.7 4.6	6.7 5.1	ns

NOTE:
1. All typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.

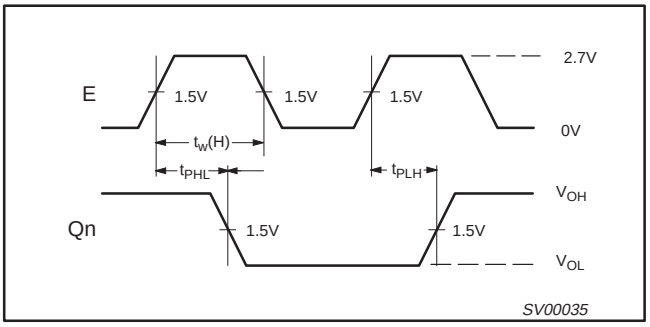
AC SETUP REQUIREMENTS

GND = 0V, $t_R = t_F$ = 2.5ns, C_L = 50pF, R_L = 500Ω; T_{amb} = –40°C to +85°C.

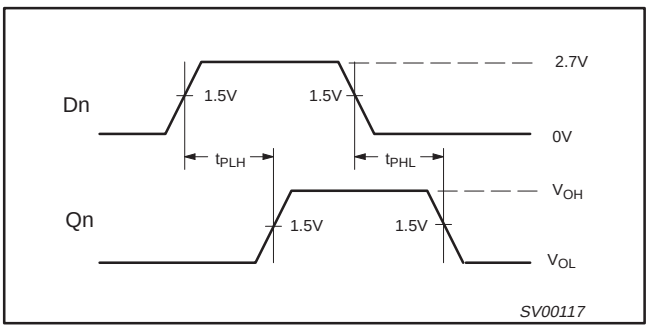
SYMBOL	PARAMETER	WAVEFORM	LIMITS			UNIT
			V_{CC} = 3.3V ± 0.3V		V_{CC} = 2.7V	
			MIN	MAX	MIN	
$t_S(H)$ $t_S(L)$	Setup time, High or Low, Dn to E	3	0.7 0.7		0.6 0.6	ns
$T_H(H)$ $T_H(L)$	Hold time, High or Low, Dn to E	3	1.6 1.6		1.8 1.8	ns
$T_W(H)$	E pulse width High	1	3.3		3.3	ns

AC WAVEFORMS

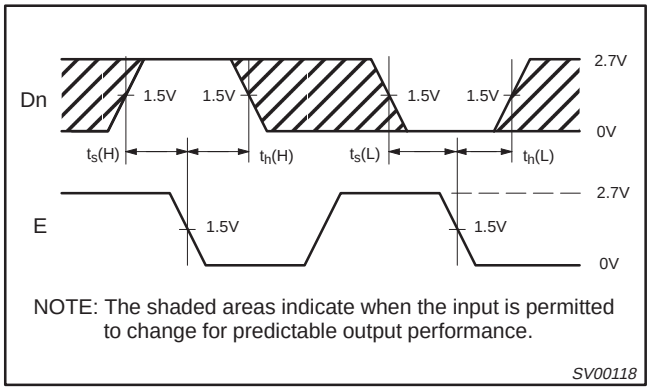
V_M = 1.5V, V_{IN} = GND to 2.7V



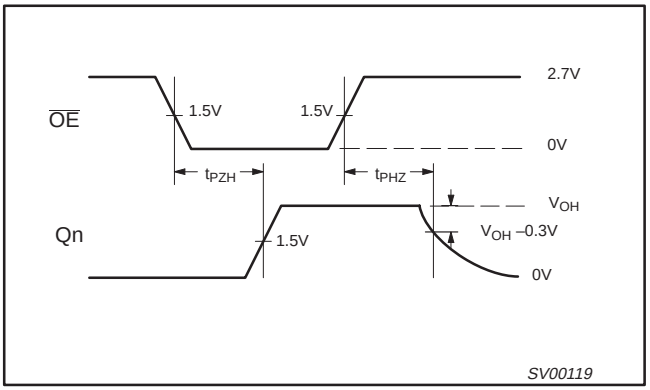
Waveform 1. Propagation Delay, Enable to Output, and Enable Pulse Width



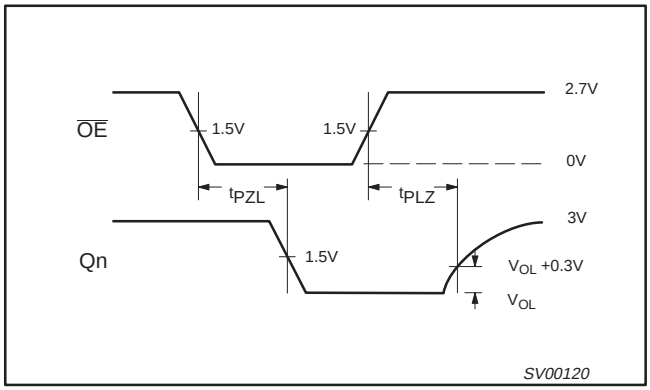
Waveform 2. Propagation Delay for Data to Outputs



Waveform 3. Data Setup and Hold Times

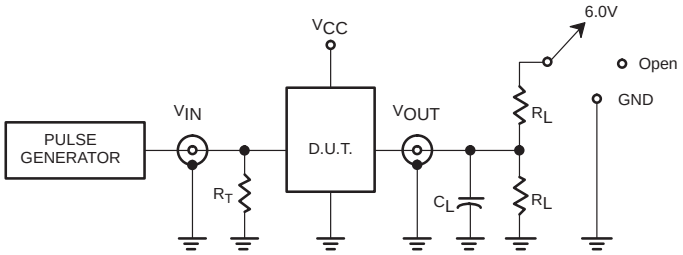


Waveform 4. 3-State Output Enable Time to High Level and Output Disable Time from High Level

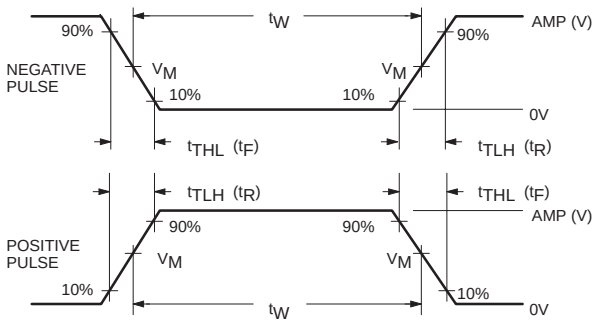


Waveform 5. 3-State Output Enable Time to Low Level and Output Disable Time from Low Level

TEST CIRCUIT AND WAVEFORM



Test Circuit for 3-State Outputs



V_M = 1.5V
Input Pulse Definition

SWITCH POSITION

TEST	SWITCH
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6V
t_{PHZ}/t_{PZH}	GND

DEFINITIONS

R_L = Load resistor; see AC CHARACTERISTICS for value.

C_L = Load capacitance includes jig and probe capacitance; see AC CHARACTERISTICS for value.

R_T = Termination resistance should be equal to Z_{OUT} of pulse generators.

FAMILY	INPUT PULSE REQUIREMENTS				
	Amplitude	Rep. Rate	t_W	t_R	t_F
74LVT	2.7V	≤10MHz	500ns	≤2.5ns	≤2.5ns

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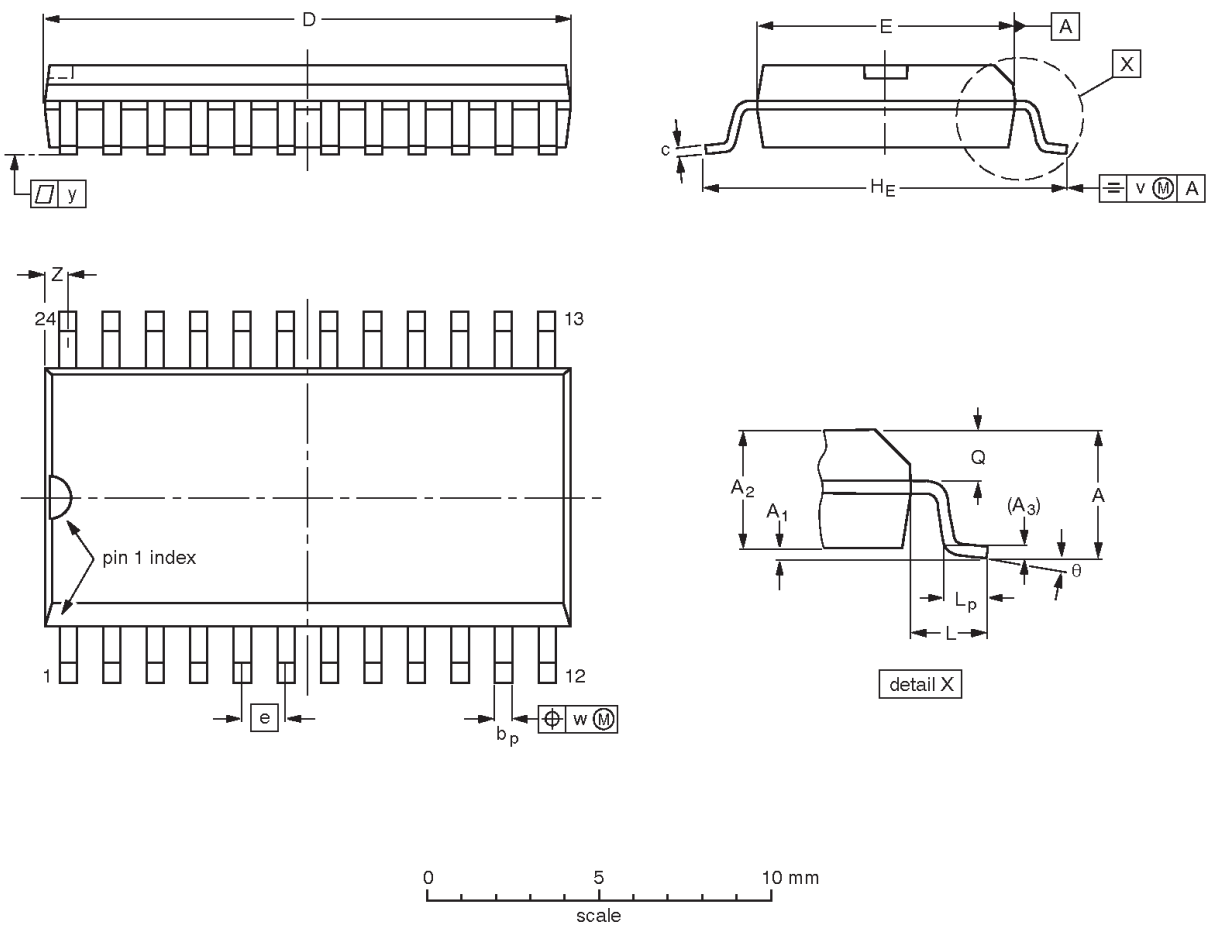
SO24: plastic small outline package; 24 leads; body width 7.5 mm **SOT137-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

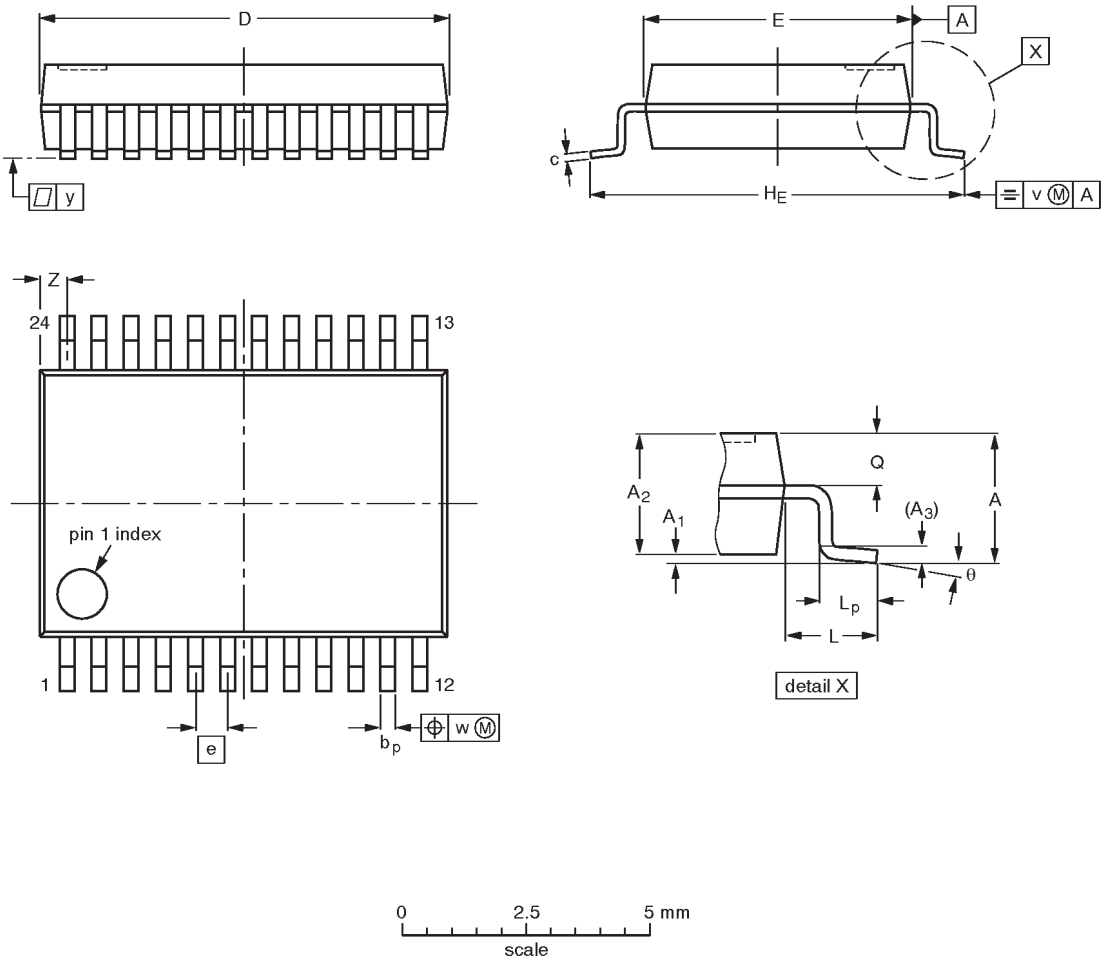
UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2.65	0.30 0.10	2.45 2.25	0.25	0.49 0.36	0.32 0.23	15.6 15.2	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8^o 0^o
inches	0.10	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.61 0.60	0.30 0.29	0.050	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT137-1	075E05	MS-013AD				~~95-01-24~~ 97-05-22

SSOP24: plastic shrink small outline package; 24 leads; body width 5.3 mm **SOT340-1**



DIMENSIONS (mm are the original dimensions)

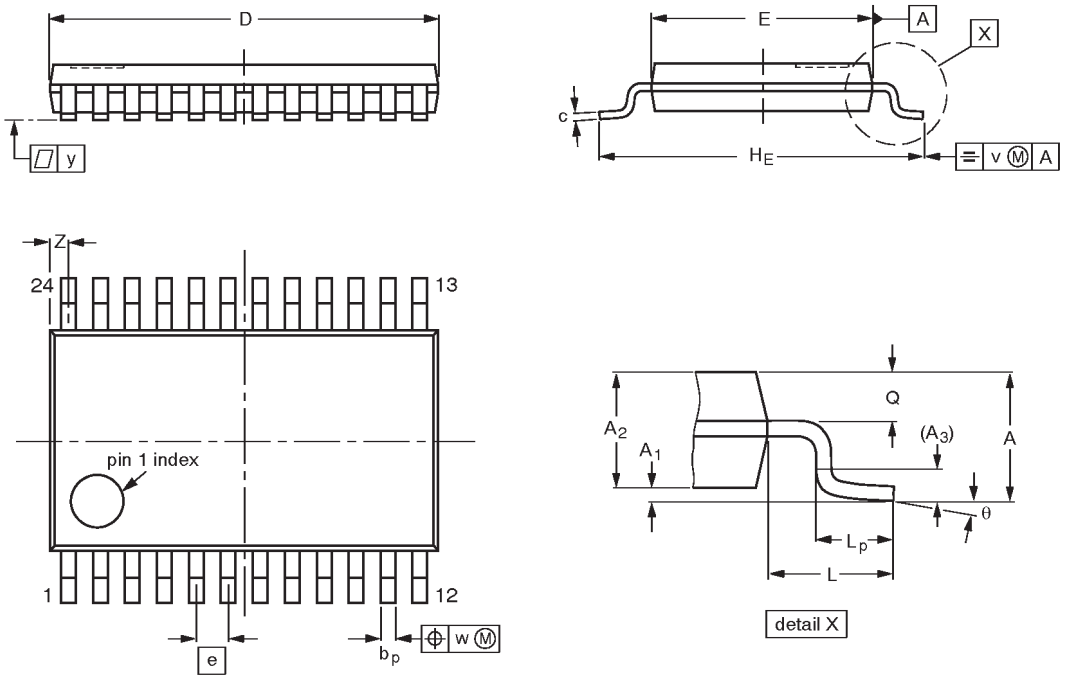
UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	8.4 8.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.8 0.4	8° 0°

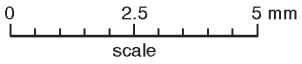
Note

1. Plastic or metal protrusions of 0.20 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT340-1		MO-150AG				~~93-09-08~~ 95-02-04

TSSOP24: plastic thin shrink small outline package; 24 leads; body width 4.4 mm SOT355-1





DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	7.9 7.7	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT355-1		MO-153AD				~~93-06-16~~ 95-02-04

NOTES

Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make chages at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

[1] Please consult the most recently issued datasheet before initiating or completing a design.

Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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